

In th Claims

CLAIMS

Claims 1-35 (Previously Cancelled).

36. (Previously Amended) A conductive line comprising:

a polysilicon layer supported by a substrate;

E1 a doped metal-silicide layer supported by the polysilicon layer, the metal-silicide layer comprising a Group III dopant or a Group V dopant provided to a concentration of at least about 1×10^{18} ions/cm³; and

a silicon-dioxide-containing dopant barrier layer elevationally over the metal-silicide layer and substrate, and the barrier layer against only the metal-silicide layer with respect to portions of the substrate laterally outward of the metal-silicide layer.

Claims 37-41 (Previously Cancelled).

42. (Previously Added) The conductive line of claim 36 wherein the metal-silicide layer comprises tantalum.

43. (Previously Added) The conductive line of claim 36 further comprising a source/drain region formed in the substrate substantially laterally outward of the conductive line.

E' 44. (Previously Added) The conductive line of claim 43 further comprising a field oxide region formed in the substrate laterally spaced from the conductive line, wherein the source/drain regions are formed within a portion of the substrate comprising substantially an entirety of the space between the field oxide region and the conductive line.
